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[54] BURIED FIELD SHIELD FOR AN INTEGRATED CIRCUIT

Paul E. Cade, Colchester; Badih [75] Inventors: El-Kareh, Milton; Ick W. Kim, St.

Albans, all of Vt.

International Business Machines [73] Assignee:

Corporation, Armonk, N.Y.

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29/577 C; 29/580; 148/DIG. 25; 148/DIG. 50; 148/DIG. 135; 148/187

[58] Field of Search 29/576 W, 576 E, 571,

29/577 C, 580; 148/DIG. 26, DIG. 25, DIG. 50, DIG. 135, 187; 357/34, 49, 53

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Primary Examiner-Aaron Weisstuch Assistant Examiner-T. Quach Attorney, Agent, or Firm-Sughrue, Mion, Zinn, Macpeak, and Seas

ABSTRACT

A method for fabrication of a buried field shield in a semiconductor substrate. A seed substrate is prepared by depositing an epitaxial layer or a seed wafer and then depositing a heavily doped layer and a thin dielectric. The thin dielectric is patterned for contact holes and then a conductive field shield is deposited and patterned. A thick quartz layer is deposited over the field shield and dielectric. A mechanical substrate is anodically bonded to the quartz of the seed substrate and the original seed wafer is etched back to expose the epitaxial layer for further fabrication.

10 Claims, 17 Drawing Figures

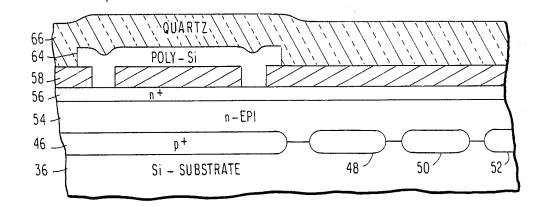
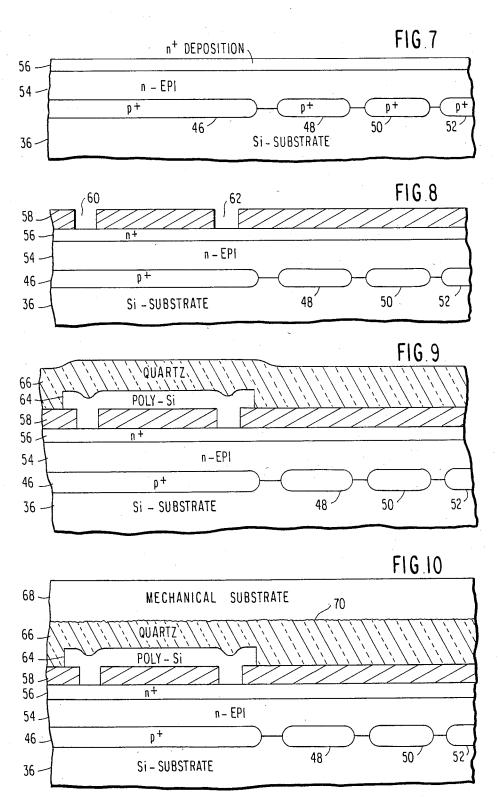
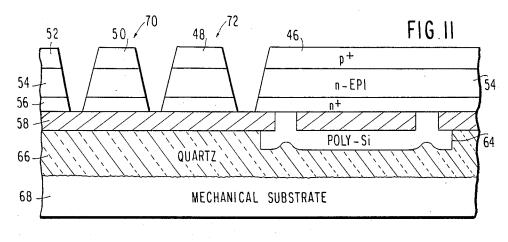
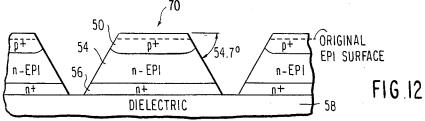


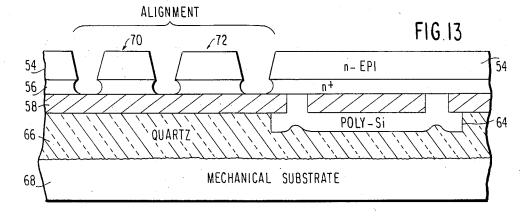


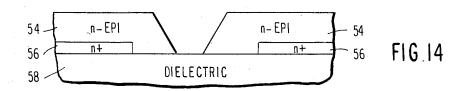
FIG.2 PRIOR ART FIG I PRIOR ART 22 p⁺ -Si SEED WAFER, 20 SEED WAFER, 20 EPITAXIAL Si 24 EPITAXIAL Si p⁺ – Si 22. 26 Si SUBSTRATE 28 FIG. 3 PRIOR ART FIG.4 EPITAXIAL Si Si SUBSTRATE 28 VII FIG.5 <u>30</u> - 34 <u>32</u> 481 50′ Si 36 <u>36</u> FIG.6 Si

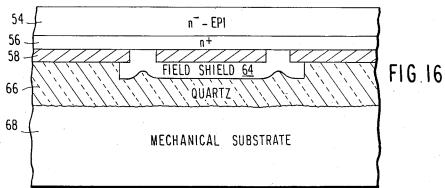


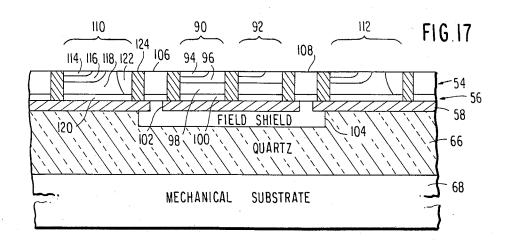












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